



74V1T70

SINGLE BUFFER

- HIGH SPEED: $t_{PD} = 5.5 \text{ ns}$ (TYP.) at $V_{CC} = 5V$
- LOW POWER DISSIPATION:
 $I_{CC} = 1 \mu\text{A}$ (MAX.) at $T_A = 25^\circ\text{C}$
- COMPATIBLE WITH TTL OUTPUTS:
 $V_{IH} = 2V$ (MIN), $V_{IL} = 0.8V$ (MAX)
- POWER DOWN PROTECTION ON INPUT
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 8 \text{ mA}$ (MIN)
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \cong t_{PHL}$
- OPERATING VOLTAGE RANGE:
 V_{CC} (OPR) = 4.5V to 5.5V
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The 74V1T70 is an advanced high-speed CMOS SINGLE BUFFER fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. It has similar high speed performance of equivalent Bipolar Schottky TTL combined with true CMOS low power dissipation. The internal circuit is composed of 2 stages

PRELIMINARY DATA



S
(SOT23-5L)



C
(SC-70)

ORDER CODE:

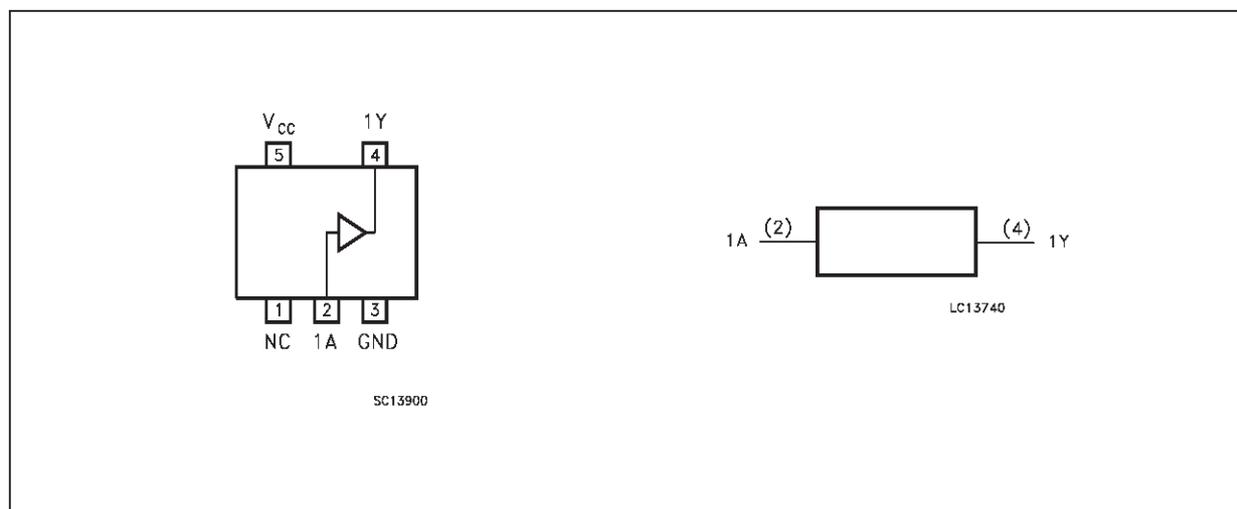
74V1T70S

74V1T70C

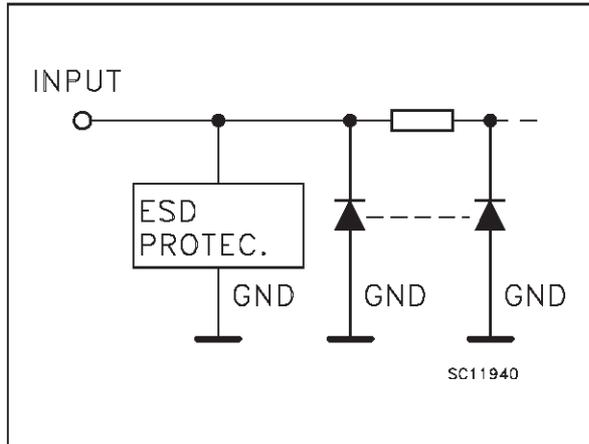
including buffer output, which provide high noise immunity and stable output.

Power down protection is provided on input and 0 to 7V can be accepted on input with no regard to the supply voltage. This device can be used to interface 5V to 3V.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

| PIN No | SYMBOL | NAME AND FUNCTION |
|--------|-----------------|-------------------------|
| 1 | N.C. | Not Connected |
| 2 | 1A | Data Input |
| 4 | 1Y | Data Output |
| 3 | GND | Ground (0V) |
| 5 | V _{CC} | Positive Supply Voltage |

TRUTH TABLE

| A | Y |
|---|---|
| L | L |
| H | H |

ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|-------------------------------------|--------------------------------------|-------------------------------|------|
| V _{CC} | Supply Voltage | -0.5 to +7.0 | V |
| V _I | DC Input Voltage | -0.5 to +7.0 | V |
| V _O | DC Output Voltage | -0.5 to V _{CC} + 0.5 | V |
| I _{IK} | DC Input Diode Current | - 20 | mA |
| I _{OK} | DC Output Diode Current | ± 20 | mA |
| I _O | DC Output Current | ± 25 | mA |
| I _{CC} or I _{GND} | DC V _{CC} or Ground Current | ± 50 | mA |
| T _{stg} | Storage Temperature | -65 to +150 | °C |
| T _L | Lead Temperature (10 sec) | 260 | °C |

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Value | Unit |
|-----------------|--|----------------------|------|
| V _{CC} | Supply Voltage | 4.5 to 5.5 | V |
| V _I | Input Voltage | 0 to 5.5 | V |
| V _O | Output Voltage | 0 to V _{CC} | V |
| T _{op} | Operating Temperature | -40 to +85 | °C |
| dt/dv | Input Rise and Fall Time (see note 1) (V _{CC} = 5.0 ± 0.5V) | 0 to 20 | ns/V |

1) V_{IN} from 0.8V to 2V

DC SPECIFICATIONS

| Symbol | Parameter | Test Conditions | | Value | | | | | Unit | | |
|------------------|--------------------------------------|-----------------|------------------|--|------|------|--------------|------|------|------|----|
| | | | | T _A = 25 °C | | | -40 to 85 °C | | | | |
| | | | | Min. | Typ. | Max. | Min. | Max. | | | |
| V _{IH} | High Level Input Voltage | 4.5 to 5.5 | | 2 | | | 2 | | V | | |
| V _{IL} | Low Level Input Voltage | 4.5 to 5.5 | | | | 0.8 | | 0.8 | V | | |
| V _{OH} | High Level Output Voltage | 4.5 | V _I = | I _O =-50 μA | 4.4 | 4.5 | | 4.4 | | V | |
| | | 4.5 | V _{IH} | I _O =-8 mA | 3.94 | | | 3.8 | | | |
| V _{OL} | Low Level Output Voltage | 4.5 | V _I = | I _O =50 μA | | 0.0 | | 0.1 | | V | |
| | | 4.5 | V _{IL} | I _O =8 mA | | | | 0.36 | 0.44 | | |
| I _I | Input Leakage Current | 0 to 5.5 | | V _I = 5.5V or GND | | | | ±0.1 | | ±1.0 | μA |
| I _{CC} | Quiescent Supply Current | 5.5 | | V _I = V _{CC} or GND | | | | 1 | | 10 | μA |
| ΔI _{CC} | Additional Worst Case Supply Current | 5.5 | | One Input at 3.4V, other input at V _{CC} or GND | | | | 1.35 | | 1.5 | mA |

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3 ns)

| Symbol | Parameter | Test Condition | | | Value | | | | | Unit | |
|------------------|------------------------|---------------------|----------------|--|------------------------|------|------|--------------|------|------|----|
| | | | | | T _A = 25 °C | | | -40 to 85 °C | | | |
| | | | | | Min. | Typ. | Max. | Min. | Max. | | |
| t _{PLH} | Propagation Delay Time | V _{CC} (*) | C _L | | | | | | | | ns |
| t _{PHL} | | (V) | (pF) | | | | | | | | |
| | | 5.0 | 15 | | | 4.7 | 6.7 | 1.0 | 7.5 | | |
| | | 5.0 | 50 | | | 5.5 | 7.7 | 1.0 | 8.5 | | |

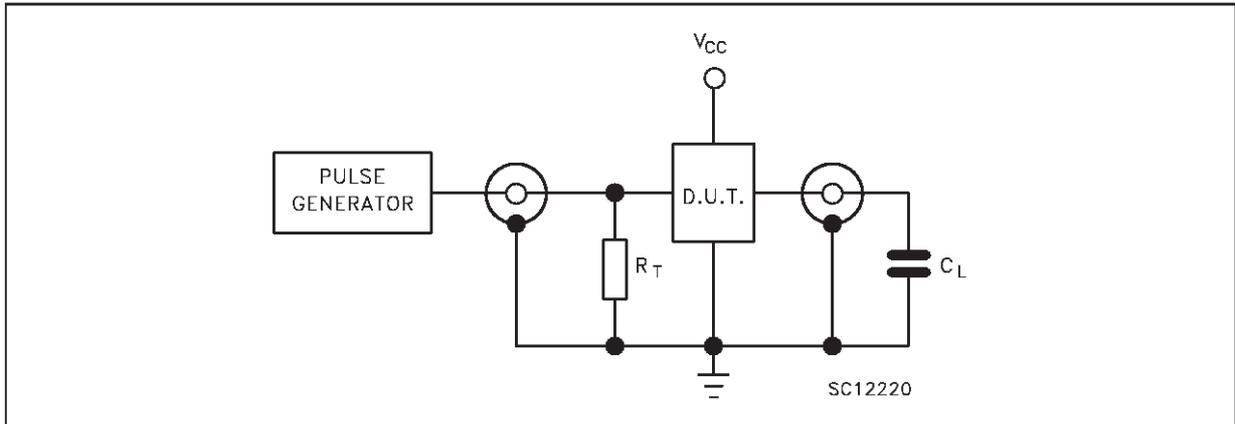
(*) Voltage range is 5V ± 0.5V

CAPACITIVE CHARACTERISTICS

| Symbol | Parameter | Test Conditions | | Value | | | | | Unit |
|-----------------|--|-----------------|--|------------------------|------|------|--------------|------|------|
| | | | | T _A = 25 °C | | | -40 to 85 °C | | |
| | | | | Min. | Typ. | Max. | Min. | Max. | |
| C _{IN} | Input Capacitance | | | 4 | 10 | | | 10 | pF |
| C _{PD} | Power Dissipation Capacitance (note 1) | | | 11 | | | | | pF |

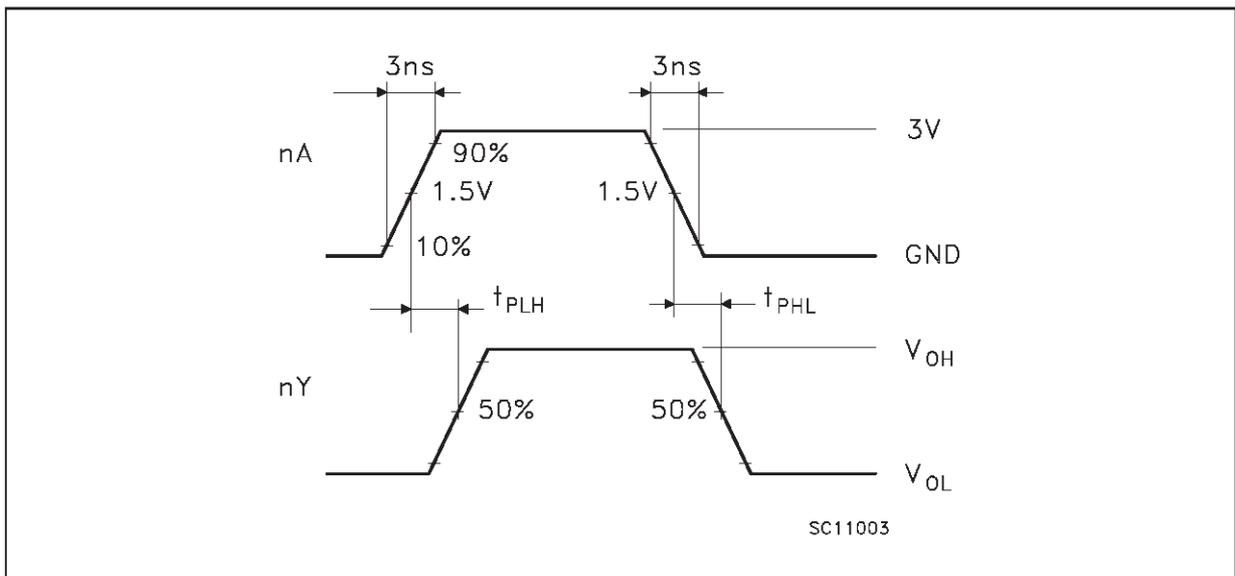
1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(opr)} = C_{PD} • V_{CC} • f_{IN} + I_{CC}

TEST CIRCUIT



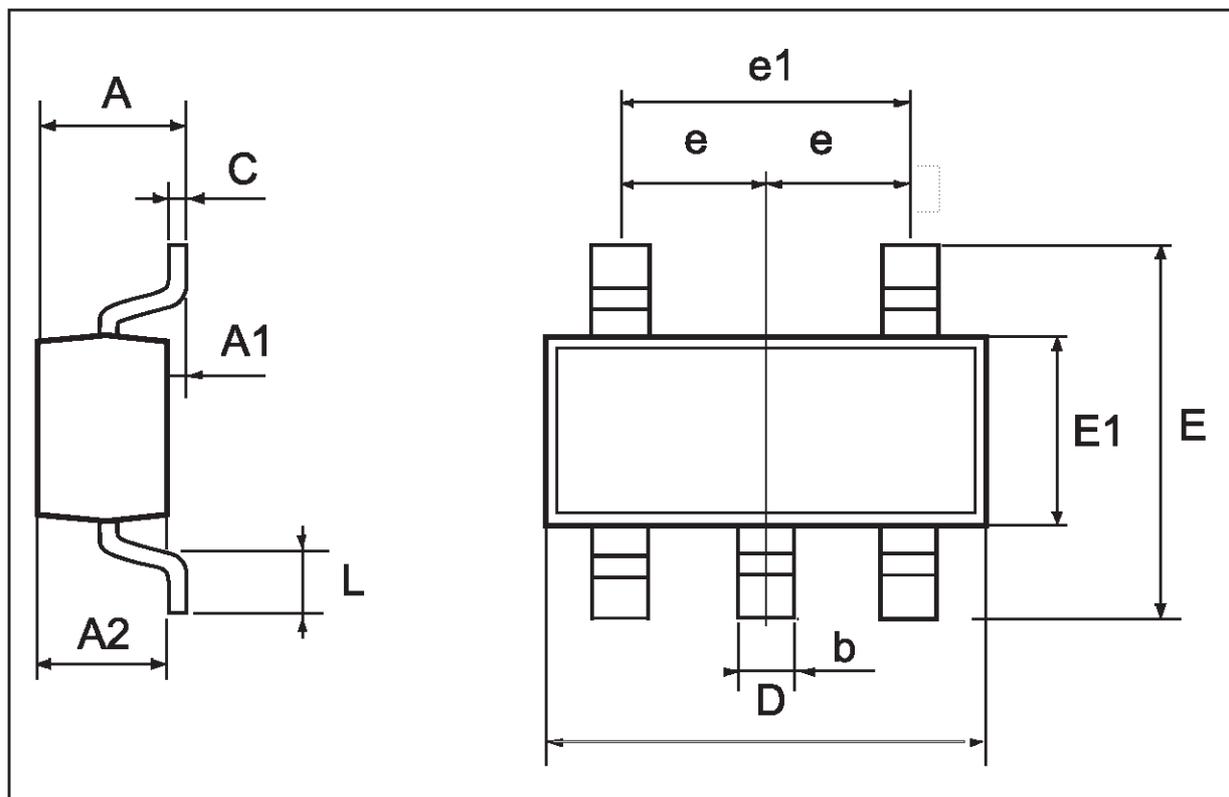
$C_L = 15/50$ pF or equivalent (includes jig and probe capacitance)
 $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)



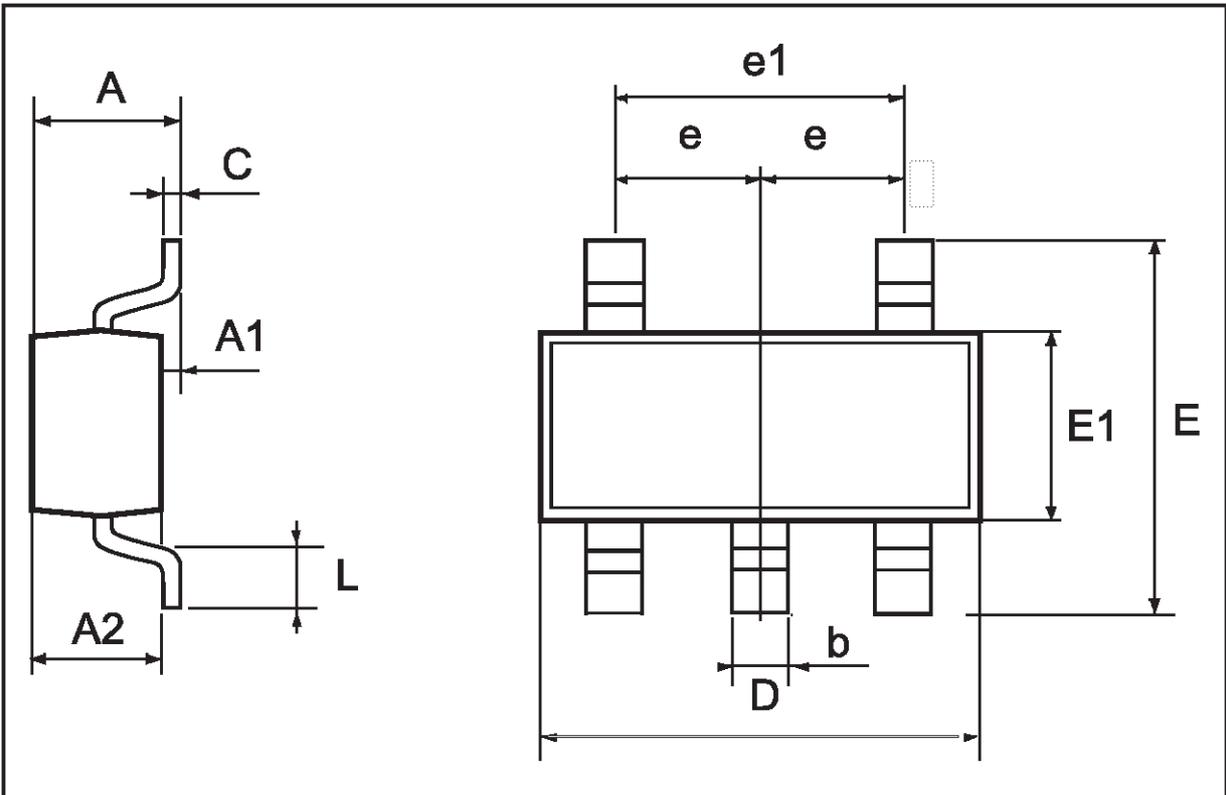
SOT23-5L MECHANICAL DATA

| DIM. | mm | | | mils | | |
|------|------|------|------|-------|------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 0.90 | | 1.45 | 35.4 | | 57.1 |
| A1 | 0.00 | | 0.15 | 0.0 | | 5.9 |
| A2 | 0.90 | | 1.30 | 35.4 | | 51.2 |
| b | 0.35 | | 0.50 | 13.7 | | 19.7 |
| C | 0.09 | | 0.20 | 3.5 | | 7.8 |
| D | 2.80 | | 3.00 | 110.2 | | 118.1 |
| E | 2.60 | | 3.00 | 102.3 | | 118.1 |
| E1 | 1.50 | | 1.75 | 59.0 | | 68.8 |
| L | 0.35 | | 0.55 | 13.7 | | 21.6 |
| e | | 0.95 | | | 37.4 | |
| e1 | | 1.9 | | | 74.8 | |



SC-70 MECHANICAL DATA

| DIM. | mm | | | mils | | |
|------|------|------|------|------|------|------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 0.80 | | 1.10 | 31.5 | | 43.3 |
| A1 | 0.00 | | 0.10 | 0.0 | | 3.9 |
| A2 | 0.80 | | 1.00 | 31.5 | | 39.4 |
| b | 0.15 | | 0.30 | 5.9 | | 11.8 |
| C | 0.10 | | 0.18 | 3.9 | | 7.1 |
| D | 1.80 | | 2.20 | 70.9 | | 86.6 |
| E | 1.80 | | 2.40 | 70.9 | | 94.5 |
| E1 | 1.15 | | 1.35 | 45.3 | | 53.1 |
| L | 0.10 | | 0.30 | 3.9 | | 11.8 |
| e | | 0.65 | | | 25.6 | |
| e1 | | 1.3 | | | 51.2 | |



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